

Attorney's Docket No.: 07977/213002/US3521/3522

REMARKS

Reconsideration and allowance of the above-referenced application are respectfully requested.

The objection to claims 8 and 19 being duplicates has been obviated by the amendment of the claims herein.

Claims 6-8 and 18-22 stand rejected under 35 U.S.C. 112, second paragraph, as allegedly being indefinite. In response, these claims are amended to obviate the rejections thereto.

Claims 6, 8-12, 14, 16, 19, and 23 stand rejected under 35 U.S.C. 102(b) as allegedly being anticipated by Zhang. This contention is respectfully traversed, and it is respectfully suggested that the rejections do not meet the Patent Office's burden of providing a *prima facie* showing of unpatentability.

Specifically, referring to the claims, Zhang does not disclose "a second metal element added region" and "a second crystalline portion". FIGS. 3A, 7A, and 8A of Zhang show only one metal element added region, respectively in regions 300, 504, and 605. They do not show a second metal element added region as claimed. Moreover, it is respectfully suggested that Zhang does not disclose a second crystalline portion, that is a portion that is crystallized by using the second metal element added region, used for a crystalline semiconductor island.

Upon review of Zhang, it appears that Zhang does not disclose that the "metal element added region has a length

Attorney's Docket No.: 07977/213002/US3521/3522

extending longer from an end portion of a crystalline semiconductor island in a longitudinal direction of the metal element added region".

This claimed feature is shown in FIG. 2A of the subject application which represents a top view of the structure. FIGS. 3B, 7C, and 8C of Zhang merely disclose a cross sectional view that does not teach or suggest this claimed feature.

For all of these reasons, it is respectfully suggested that this rejection is incorrect, and therefore, that the rejection does not meet the Patent Office's burden of providing a *prima facie* showing of unpatentability.

Claims 6-12 and 14-23 stand rejected under 35 U.S.C. 102(e) as allegedly being anticipated by Yamazaki's U.S. Patent No. 6,077,731. The verified translations of the Japanese priority applications will be filed in due course which perfect the Japanese priority date.

New claims 24-71 are also added, and recite the limitation that a length of metal element added region, and an inverter circuit, are different than those of the corresponding prior art.

In view of the above amendments and remarks, therefore, all of the claims should be in condition for allowance. A formal notice to that effect is respectfully solicited.

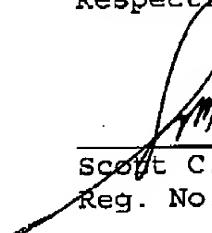
Attorney's Docket No.: 07977/213002/US3521/3522

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Respectfully submitted,

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Attorney's Docket No.: 07977/213002/US3521/3522

VERSION TO SHOW CHANGES MADEIn the Claims:

Claims 17, 19, and 22 have been canceled.

The claims have been amended as follows.

6. (Amended) A method of manufacturing a semiconductor device, said method comprising:

forming an amorphous semiconductor film on an insulating surface;

[introducing] providing a metal element being capable of promoting crystallization of the amorphous semiconductor film to form a first metal element added region and a second metal element added region;

crystallizing the amorphous semiconductor film so that a crystal growth proceeds in a crystal growth direction parallel to the insulating surface from the first metal element added region and [a] the second metal element added region thereby to form a first crystalline portion and a second crystalline portion, respectively, in a crystalline semiconductor film;

patterning the crystalline semiconductor film to form at least [a] one crystalline semiconductor island using only the first crystalline portion while the second crystalline portion is not used to form the crystalline semiconductor island,

Attorney's Docket No.: 07977/213002/US3521/3522

wherein carriers move in the crystalline semiconductor island in a carrier moving direction identical with the crystal growth direction,

wherein the second metal element added region is located apart from the crystalline semiconductor island by a distance,

wherein the first metal element added region has a length extending longer from an end portion of the crystalline semiconductor island in a longitudinal direction of the first metal element added region.

7. (Amended) A method according to claim 6,
wherein [the length] lengths of the first metal element added region and the second element added region [is] are set to 50% or more of a crystal growth distance.

9. (Amended) A method of manufacturing a semiconductor device, said method comprising:
forming an amorphous semiconductor film on an insulating surface;
selectively [introducing] providing a metal element being capable of promoting crystallization of the amorphous semiconductor film into at least a first region and a second region of the amorphous semiconductor film to form a first metal

Attorney's Docket No.: 07977/213002/US3521/3522

element [introduced] added region and a second metal element [introduced] added region, respectively; crystallizing the amorphous semiconductor film so that a crystal [growth proceeds] growths proceed in parallel to the insulating surface from each of the first metal element added region and the second metal element [introduced regions] added region to form a first crystalline semiconductor region and a second crystalline semiconductor region, respectively;

forming at least [a] one active region of the semiconductor device in the first crystalline semiconductor region while the second crystalline semiconductor region is not used to form an active region of the semiconductor device.

11. (Amended) A method according to claim 9, wherein the metal element is [introduced] provided by an ion implanting method.

12. (Amended) A method according to claim 9, wherein the metal element is [introduced] provided by coating a solvent comprising the metal element.

14. (Amended) A method according to claim 9, wherein the amorphous semiconductor film comprises silicon.

18. (Amended) A method according to claim 6,

Attorney's Docket No.: 07977/213002/US3521/3522

wherein the amorphous semiconductor film comprises silicon.

23. (Amended) A method according to claim 9,
further comprising controlling crystal growth state using the
second metal element [introduced] added region.

New claims 24-71 have been added.